Interface-controlled growth of organic semiconductors on graphene

Jinta Mathew, Saim Emin, Egon Pavlica, Matjaž Valant,
Gvido Bratina

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Highlights

- PDIF-CN2 forms irregularly-shaped 1.4 nm-high islands on bilayer and multilayer graphene.
- Electric force microscopy reveals higher surface charge density on single-layer graphene than on the bilayer graphene.
- No PDIF-CN2 nucleation is observed on single-layer graphene on SiO2.
- PDIF-CN2 nucleates on unsupported single-layer graphene.